

	Type	L #	Hits	Search Text	DBs	Time Stamp
1	BRS	L9	0	((second third alternat\$4) adj1 (insulat\$4 cladd\$4) near1 layer\$1) and ((second third alternat\$4) adj1 (conduct\$4) adj1 layer\$1) same wire\$1) and ((insulat\$4 cladd\$4) near1 layer\$1) near7 (substrat\$2) same (si silicon silicate)) and ((platform\$1 IC integrated adj1 circuit\$1) near12 (si silicon silicate))	EPO; JPO; DERWENT	2004/10/25 15:41
2	BRS	L10	0	((second third alternat\$4) adj1 (insulat\$4 cladd\$4) near1 layer\$1) and ((second third alternat\$4) adj1 (conduct\$4) adj1 layer\$1) same wire\$1) and ((insulat\$4 cladd\$4) near1 layer\$1) near7 (substrat\$2) same (si silicon silicate))	EPO; JPO; DERWENT	2004/10/25 15:41
3	BRS	L11	14	((second third alternat\$4) adj1 (insulat\$4 cladd\$4) near1 layer\$1) and ((second third alternat\$4) adj1 (conduct\$4) adj1 layer\$1) same wire\$1) and ((insulat\$4 cladd\$4) near1 layer\$1) near7 (substrat\$2) same (si silicon silicate))	USPAT; US-PGPU B	2004/10/25 16:12
4	BRS	L13	760	257/81,82.ccls.	USPAT; US-PGPU B	2004/10/25 16:11
5	BRS	L14	43	13 and (conduct\$4 near7 layer\$1) and ((insulat\$4 cladd\$4) near7 layer\$1) and silicon same (ic integrated near1 circuit\$4 platform carrier)	USPAT; US-PGPU B	2004/10/25 16:15
6	BRS	L15	31955	385/\$.ccls.	USPAT; US-PGPU B	2004/10/25 16:15
7	BRS	L16	169	15 and (conduct\$4 near7 layer\$1) and ((insulat\$4 cladd\$4) near7 layer\$1) and silicon same (ic integrated near1 circuit\$4 platform carrier)	USPAT; US-PGPU B	2004/10/25 16:29
8	BRS	L17	209	14 16	USPAT; US-PGPU B	2004/10/25 16:27
9	BRS	L18	8	(5,150,280 6,384,509 5,557,115 6,333,598 'WO 8704565' 6,343,171 5,315,140 5,714,773 6,164,836).PN.	USPAT; US-PGPU B	2004/10/25 16:28
10	BRS	L19	8	18 and ((conduct\$4 insulat\$4 cladd\$4) same layer\$1) and (si silicon ic integrated near1 circuit\$4 platform carrier)	USPAT; US-PGPU B	2004/10/25 16:34
11	BRS	L20	7	18 and ((conduct\$4) same (insulat\$4 cladd\$4)) and (si silicon ic integrated near1 circuit\$4 platform carrier pin\$1 wire\$1)	USPAT; US-PGPU B	2004/10/25 17:59

	Comments	Error Definition	Errors
1			0
2			0
3			0
4			0
5			0
6			0
7			0
8			0
9			0
10			0
11			0

	Type	Hits	Search Text
1	BRS	1	5150280.pn.
2	BRS	1	5150280.pn. and (si silic\$4 substrat\$4)
3	BRS	0	09/767231.pn.
4	BRS	15470	((second third alternat\$4) adj1 (insulat\$4 cladd\$4) near1 layer\$1)
5	BRS	433	((second third alternat\$4) adj1 (conduct\$4) adj1 layer\$1) same wire\$1
6	BRS	18630	((insulat\$4 cladd\$4) near1 layer\$1) near7 (substrat\$2) same (si silicon silicate)
7	BRS	35038	(platform\$1 IC integrated adj1 circuit\$1) near12 (si silicon silicate)
8	BRS	1	((second third alternat\$4) adj1 (insulat\$4 cladd\$4) near1 layer\$1) and (((second third alternat\$4) adj1 (conduct\$4) adj1 layer\$1) same wire\$1) and (((insulat\$4 cladd\$4) near1 layer\$1) near7 (substrat\$2) same (si silicon silicate)) and ((platform\$1 IC integrated adj1 circuit\$1) near12 (si silicon silicate))

	DBs	Time Stamp	Comments	Error Definition
1	USPAT; US-PGPUB	2004/10/25 13:08		
2	USPAT; US-PGPUB	2004/10/25 14:08		
3	USPAT; US-PGPUB	2004/10/25 14:09		
4	USPAT; US-PGPUB	2004/10/25 14:17		
5	USPAT; US-PGPUB	2004/10/25 14:23		
6	USPAT; US-PGPUB	2004/10/25 14:33		
7	USPAT; US-PGPUB	2004/10/25 14:34		
8	USPAT; US-PGPUB	2004/10/25 15:40		

	Errors
1	0
2	0
3	0
4	0
5	0
6	0
7	0
8	0